Preferred Device

# **General Purpose Transistor**

## **NPN Silicon**

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-723 package which is designed for low power surface mount applications.

• This is a Pb-Free Device

#### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	45	V
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current – Continuous	I <sub>C</sub>	100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) T <sub>A</sub> = 25°C	P <sub>D</sub>	260	mW
Derated above 25°C		2.0	mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	480	°C/W
Total Device Dissipation, FR-4 Board (Note 2) T <sub>A</sub> = 25°C	P <sub>D</sub>	600	mW
Derated above 25°C		4.8	mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	205	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

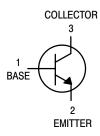
1. FR-4 @ Minimum Pad

- 2. FR-4 @ 1.0 × 1.0 Inch Pad



#### ON Semiconductor®

#### http://onsemi.com







1F = Device Code M = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BC847BM3T5G	SOT-723	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA)	V <sub>(BR)CEO</sub>	45	_	-	V
Collector – Emitter Breakdown Voltage ( $I_C = 10 \mu A, V_{EB} = 0$ )	V <sub>(BR)CES</sub>	50	-	-	V
Collector – Base Breakdown Voltage ( $I_C = 10 \mu A$ )	V <sub>(BR)CBO</sub>	50	_	-	V
Emitter – Base Breakdown Voltage ( $I_E = 1.0 \mu A$ )	V <sub>(BR)EBO</sub>	6.0	_	-	V
Collector Cutoff Current $(V_{CB} = 30 \text{ V})$ $(V_{CB} = 30 \text{ V}, T_{A} = 150^{\circ}\text{C})$	I <sub>CBO</sub>	-		15 5.0	nA μA
ON CHARACTERISTICS	•		•		*
DC Current Gain $ (I_C = 10 \ \mu\text{A}, \ V_{CE} = 5.0 \ \text{V}) $ $ (I_C = 2.0 \ \text{mA}, \ V_{CE} = 5.0 \ \text{V}) $	h <sub>FE</sub>	_ 200	150 290	- 450	_
Collector – Emitter Saturation Voltage ( $I_C$ = 10 mA, $I_B$ = 0.5 mA) ( $I_C$ = 100 mA, $I_B$ = 5.0 mA)	V <sub>CE(sat)</sub>	- -	_ _	0.25 0.6	V
Base – Emitter Saturation Voltage ( $I_C = 10 \text{ mA}$ , $I_B = 0.5 \text{ mA}$ ) ( $I_C = 100 \text{ mA}$ , $I_B = 5.0 \text{ mA}$ )	V <sub>BE(sat)</sub>	-	0.7 0.9	- -	V
Base – Emitter Voltage ( $I_C$ = 2.0 mA, $V_{CE}$ = 5.0 V) ( $I_C$ = 10 mA, $V_{CE}$ = 5.0 V)	V <sub>BE(on)</sub>	580 -	660 -	700 770	mV
SMALL-SIGNAL CHARACTERISTICS	1			•	•
Current – Gain – Bandwidth Product ( $I_C = 10$ mA, $V_{CE} = 5.0$ Vdc, $f = 100$ MHz)	f <sub>T</sub>	100	_	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 V, f = 1.0 MHz)	C <sub>obo</sub>	-	_	4.5	pF
Noise Figure (I <sub>C</sub> = 0.2 mA, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 2.0 k $\Omega$ , f = 1.0 kHz, BW = 200 Hz)	NF	_	_	10	dB

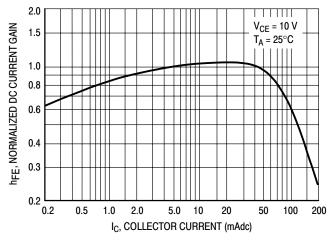


Figure 1. Normalized DC Current Gain

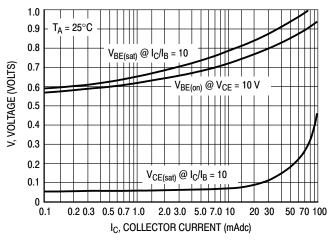


Figure 2. "Saturation" and "On" Voltages

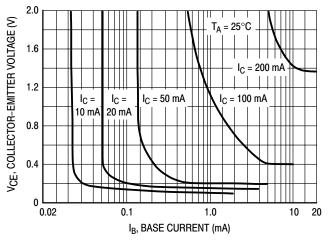


Figure 3. Collector Saturation Region

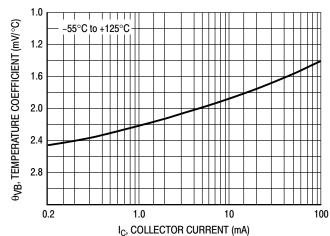
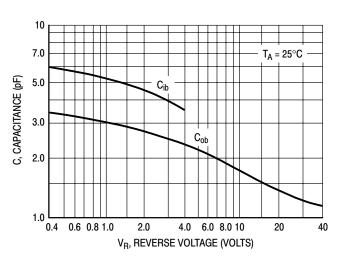


Figure 4. Base-Emitter Temperature Coefficient

#### BC847



 $f_{T}$ , CURRENT-GAIN – BANDWIDTH PRODUCT (MHz) 400 300 200  $V_{CE}$  = 10 V  $T_A$  = 25°C 100 80 60 40 30 20 0.5 0.7 1.0 2.0 3.0 5.0 7.0 10 20 30 50 I<sub>C</sub>, COLLECTOR CURRENT (mAdc)

Figure 5. Capacitances

Figure 6. Current-Gain - Bandwidth Product



SOT-723 CASE 631AA-01 ISSUE D

**DATE 10 AUG 2009** 

#### NOTES:

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
С	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
е	0.40 BSC		
ΗE	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

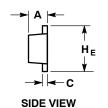
# **GENERIC** MARKING DIAGRAM\*

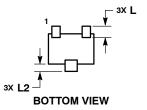


= Specific Device Code XX Μ = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

# -X-2X b ⊕ 0.08 X Y **TOP VIEW**

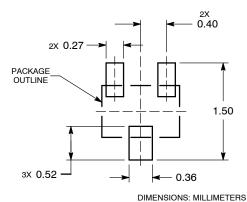




STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

**RECOMMENDED SOLDERING FOOTPRINT\*** 



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON12989D	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-723		PAGE 1 OF 1

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="https://www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems. or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales